



TR BD355;CEMI;CE24;tranzystor; PNP;3A;60V;12.5W;10MHz



Dane techniczne:

Nazwa: BD355

Typ tranzystora: bipolarny

Kierunek przewodnictwa: PNP

Prąd kolektora: 3A

Napięcie kolektor-emiter: 60V

Moc: 12.5W

Częstotliwość: 10MHz

Obudowa: CE24

Producent: CEMI

isc Silicon PNP Power Transistor
BD355
DESCRIPTION

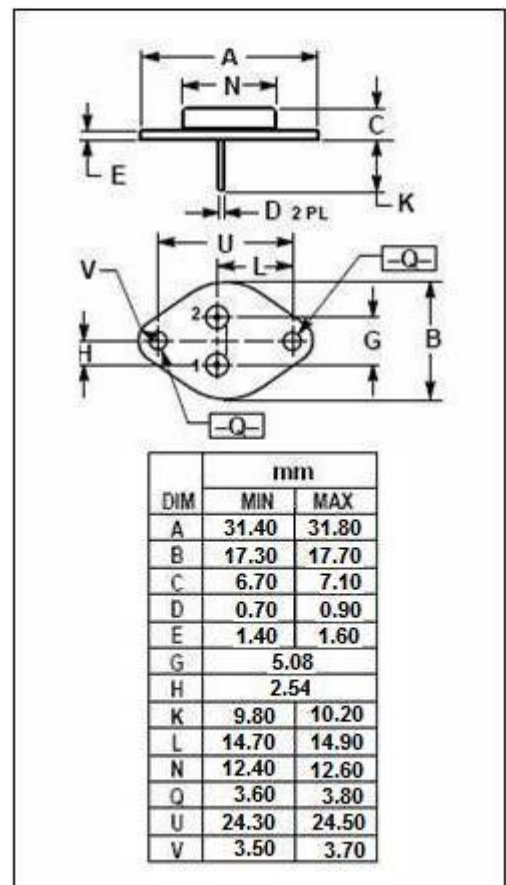
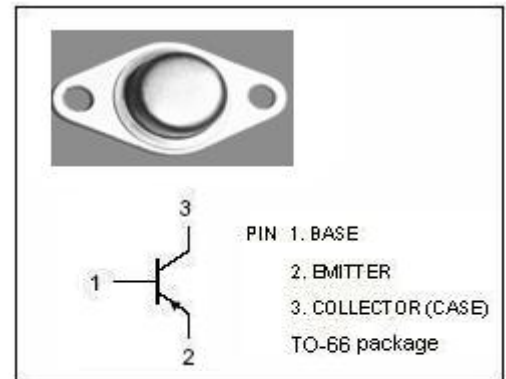
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = -60V(\text{Min})$
- Low Saturation Voltage-
: $V_{CE(\text{sat})} = -1.0V(\text{Max}) @ I_C = -2.0A$
- Excellent Safe Operating Area
- Complement to Type BD354
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for general purpose switching and amplifier applications

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-60	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-2	A
I_{CM}	Collector Current-Peak	-4	A
I_B	Base Current-Continuous	-1	A
P_C	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	25	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-65~150	$^\circ\text{C}$



isc Silicon PNP Power Transistor**BD355****ELECTRICAL CHARACTERISTICS** $T_C=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = -30\text{mA}; I_B = 0$	-60		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = -1\text{mA}; I_E = 0$	60		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = -1\text{mA}; I_C = 0$	5		V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	$I_C = -0.5\text{A}; I_B = -50\text{mA}$		-0.5	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	$I_C = -2\text{A}; I_B = -0.2\text{A}$		-1.0	V
$V_{BE(sat)-1}$	Base-Emitter Saturation Voltage	$I_C = -0.5\text{A}; I_B = -50\text{mA}$		-1.0	V
$V_{BE(sat)-2}$	Base-Emitter Saturation Voltage	$I_C = -2\text{A}; I_B = -0.2\text{A}$		-1.5	V
I_{CEO}	Collector Cutoff Current	$V_{CE} = -60\text{V}; I_B = 0$		-0.2	mA
I_{CBO}	Collector Cutoff Current	$V_{CB} = -60\text{V}; I_E = 0$		-0.1	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = -5.0\text{V}; I_C = 0$		-0.1	mA
h_{FE-1}	DC Current Gain	$I_C = -0.5\text{A}; V_{CE} = -4\text{V}$	30	150	
h_{FE-1}	DC Current Gain	$I_C = -2\text{A}; V_{CE} = -4\text{V}$	5		
f_T	Current Gain-Bandwidth Product	$I_C = -0.5\text{A}; V_{CE} = -10\text{V}; f = 1\text{MHz}$	30		MHz

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